

2ST3360

60V, 0.8A, Hi-Rel, NPN and PNP complementary transistor



The new 2ST3360, specifically designed for Space application, offers best-in-class radiation hardness performance

This product is a dual complementary NPN and PNP bipolar transistor housed in Flat-8 hermetic package. Developed from ST's rad-hard high current density bipolar technology, it ensures high switching performances and improves radiation hardness. Suitable for power MOSFET driver applications, it is qualified in the ESCC system as per 5207/009 specification.

KEY FEATURES

- 100 krad (Si) low dose rate
- Temperature range: -65 °C to 200 °C

KEY BENEFITS

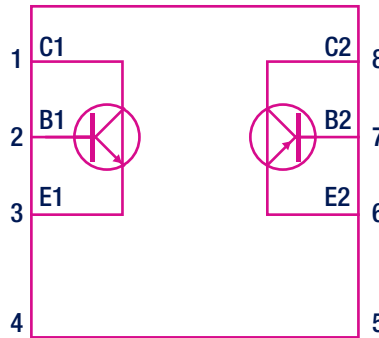
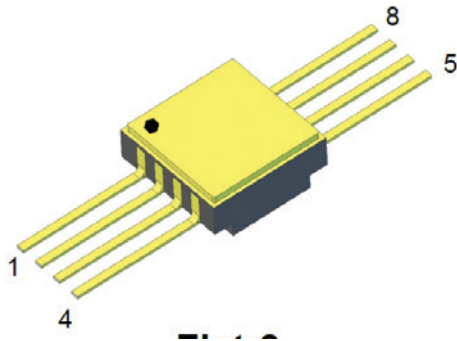
- Linear gain characteristics
- Matched pair
- High collector peak current (4A)

KEY APPLICATIONS

- Satellite
 - Telecom
 - Positioning
 - Earth observation
 - Science & Mission

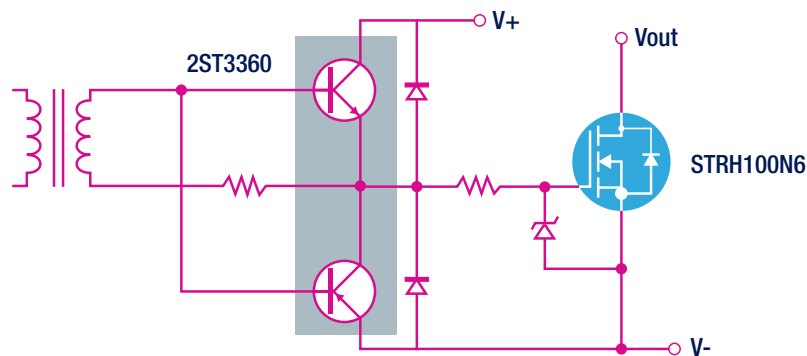


FLAT-8 PACKAGE AND SCHEME



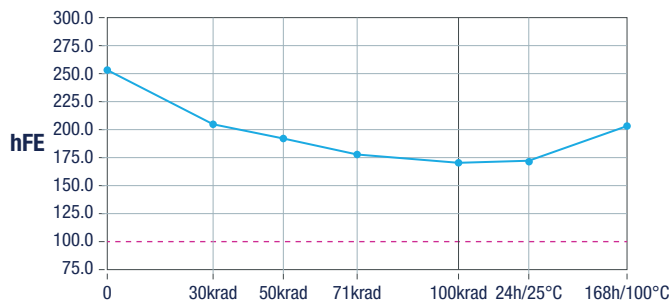
Flat-8
Pin 4 and pin 5
are connected together
to the seal ring and lid

This device has been designed to perform best-in-class switching performance in Power conversion application in satellite equipment. It is suitable to drive high gate charge of high current Power MOSFET as per below simplified schematic.

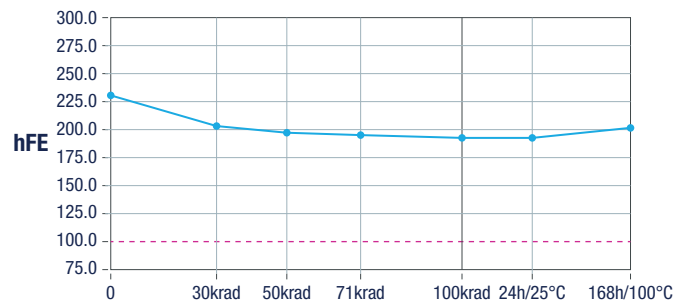


Thanks to the specific rad-hard design it offers stable performance under radiation exposure. The graphs below show the hFE behaviour vs. the total ionized dose up to 100 krad.

NPN (hFE @ Ta = 25° C ; Vce = 2 V ; Ic = 100 mA)



PNP (hFE @ Ta = 25° C ; Vce = -2 V ; Ic = -100 mA)



ORDERING INFORMATION

Part number	Agency specification	Quality level	Radiation level	Package	Mass	Lead finish	Marking
2ST3360K1	-	Engineering model	-	-	-	Gold	2ST3360K1
2ST3360RKG	5207/009/10R	ESCC flight	100 krad	Flat-8	0.4 g	Gold	520700910R
2ST3360RKT	5207/009/11R	ESCC flight	100 krad	-	-	Solder dip	520700511R

